

DESCRIPTION

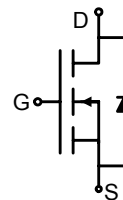
The SSFK3208 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

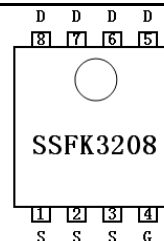
- $V_{DS} = 30V, I_D = 11A$
 $R_{DS(ON)} < 13m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 9m\Omega @ V_{GS}=10V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

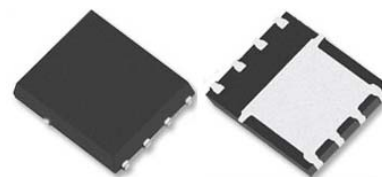
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



GEMPAK5060 top and bottom view

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
SSFK3208	SSFK3208	GEMPAK5060	-	-	-

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	11	A
	$I_D(70^\circ C)$	8.6	A
	I_{DM}	50	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.9	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =8A		9.5	13	mΩ
		V _{GS} =10V, I _D =11A		6.5	9	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =11A		20		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V, F=1.0MHz		1200		PF
Output Capacitance	C _{oss}			300		PF
Reverse Transfer Capacitance	C _{rss}			120		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =15V,V _{GS} =10V,R _{GEN} =6Ω I _D =1A		10		nS
Turn-on Rise Time	t _r			6.5		nS
Turn-Off Delay Time	t _{d(off)}			25		nS
Turn-Off Fall Time	t _f			9.7		nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =12A,V _{GS} =10V		12		nC
Gate-Source Charge	Q _{gs}			3.2		nC
Gate-Drain Charge	Q _{gd}			3.8		nC
Body Diode Reverse Recovery Time	T _{rr}	I _F =12A, dI/dt=100A/μs		24		nS
Body Diode Reverse Recovery Charge	Q _{rr}			27		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2.3A		0.74	1.2	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

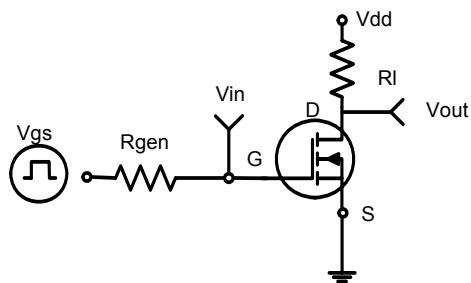


Figure 1: Switching Test Circuit

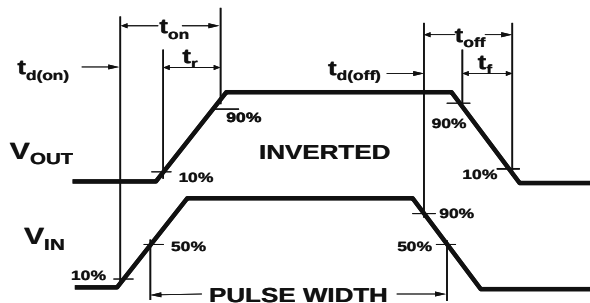


Figure 2: Switching Waveforms

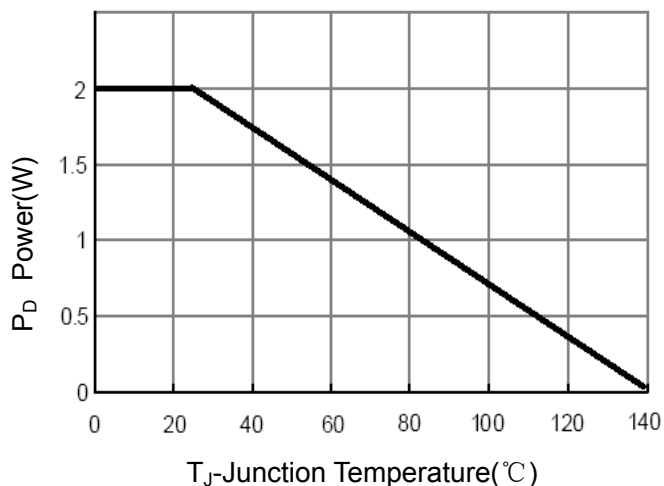


Figure 3 Power Dissipation

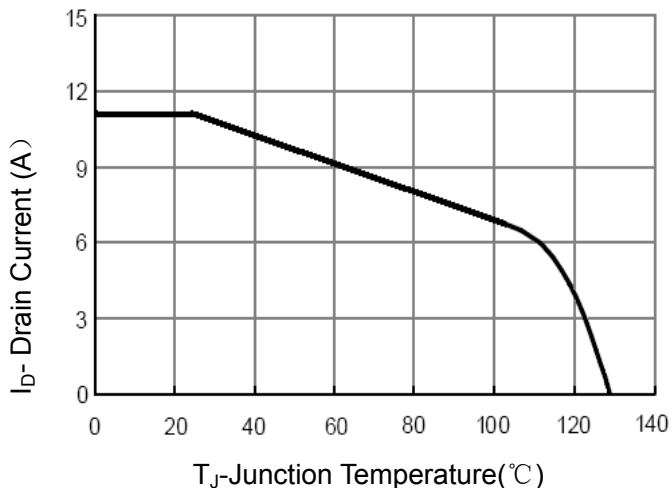


Figure 4 Drain Current

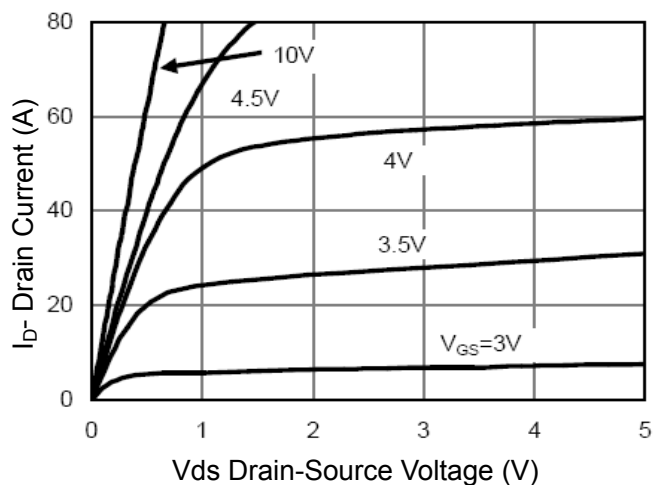


Figure 5 Output CHARACTERISTICS

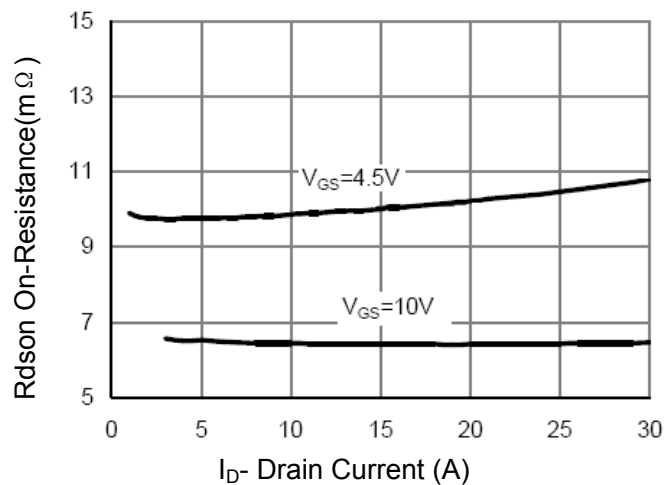


Figure 6 Drain-Source On-Resistance

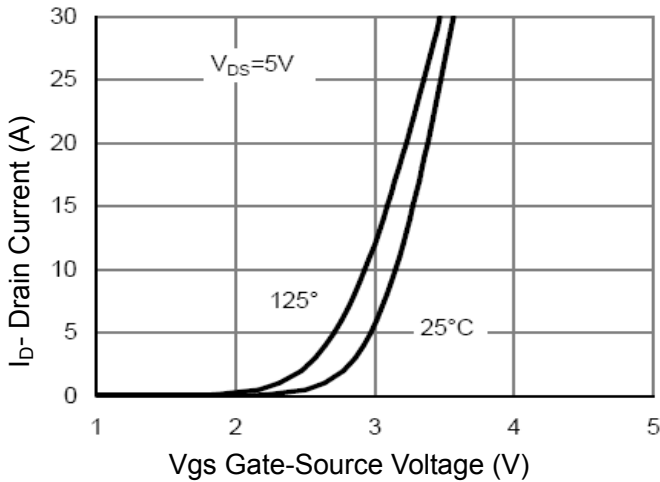


Figure 7 Transfer Characteristics

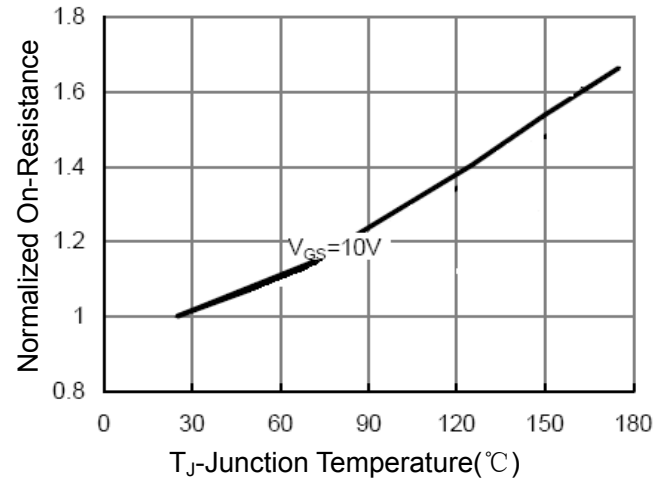


Figure 8 Drain-Source On-Resistance

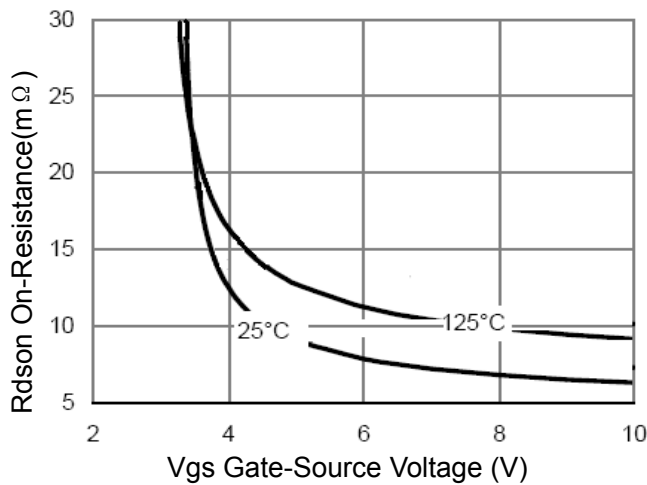


Figure 9 Rdson vs Vgs

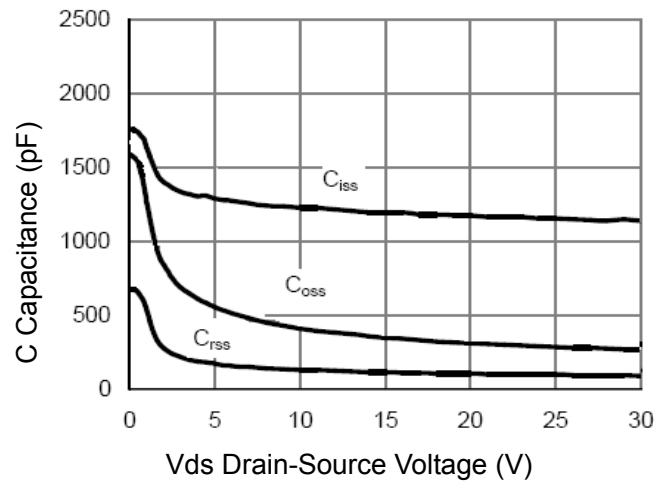


Figure 10 Capacitance vs Vds

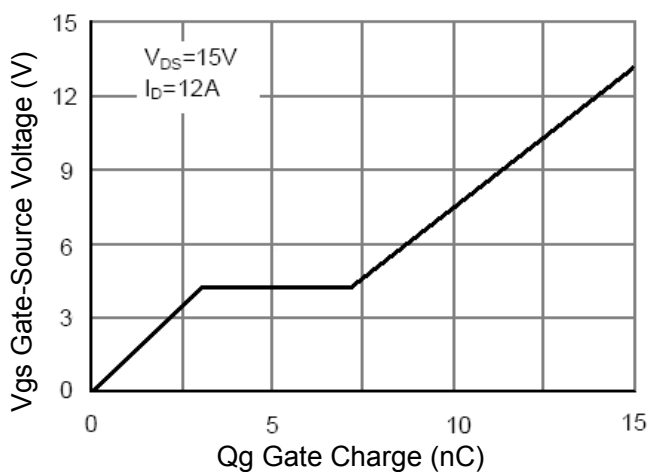


Figure 11 Gate Charge

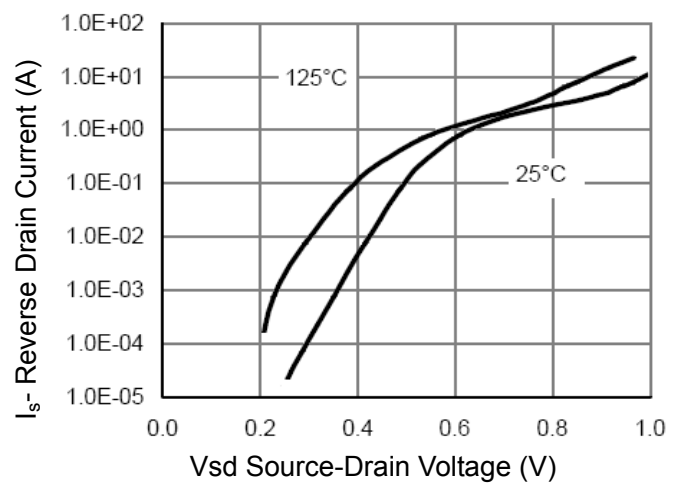


Figure 12 Source- Drain Diode Forward

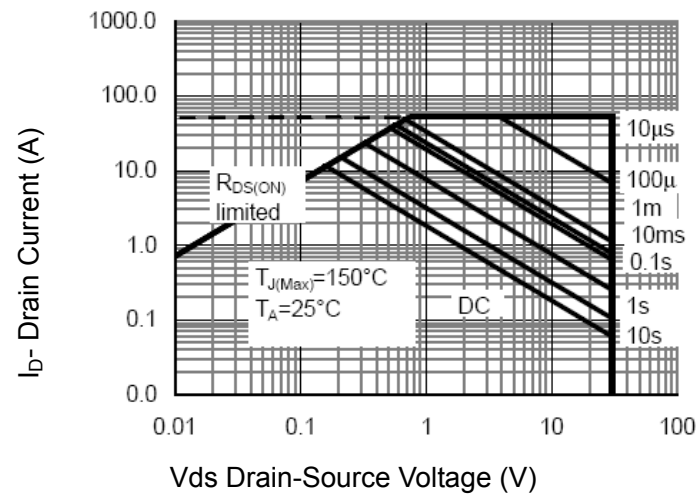


Figure 13 Safe Operation Area

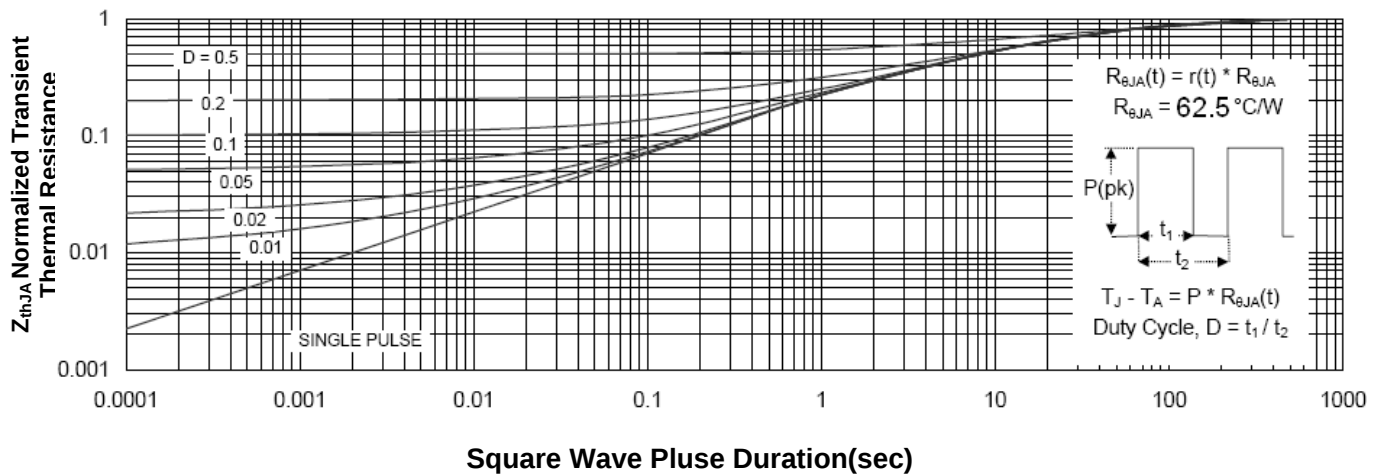
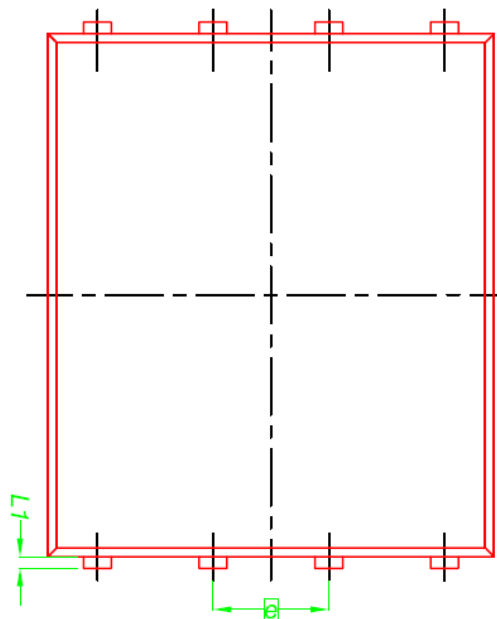
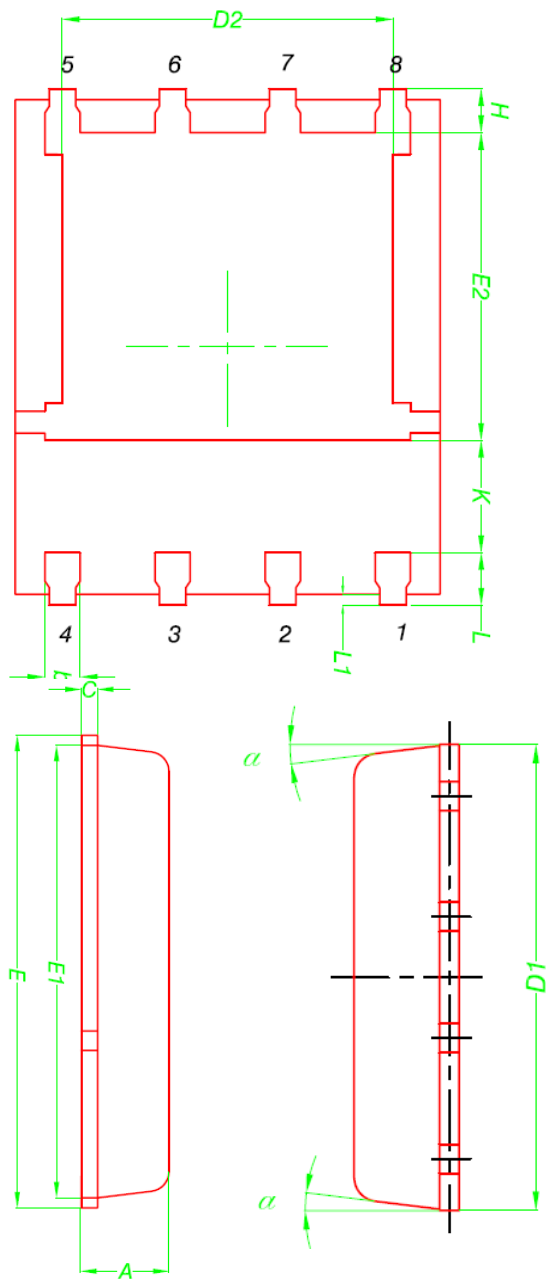


Figure 14 Normalized Maximum Transient Thermal Impedance

GEMPAK5060 PACKAGE INFORMATION



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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